

2SB0930 (2SB930), 2SB0930A (2SB930A)

Silicon PNP epitaxial planar type

For power amplification

Complementary to 2SD1253, 2SD1253A

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0930	V_{CBO}	-60	V
	2SB0930A		-80	
Collector-emitter voltage (Base open)	2SB0930	V_{CEO}	-60	V
	2SB0930A		-80	
Emitter-base voltage (Collector open)		V_{EBO}	-5	V
Collector current		I_C	-4	A
Peak collector current		I_{CP}	-8	A
Collector power dissipation	$T_a = 25^{\circ}\text{C}$	P_C	40	W
			1.3	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$

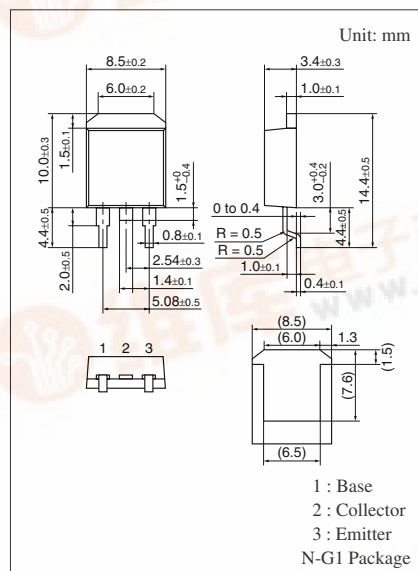
■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0930 2SB0930A	V_{CEO} $I_C = -30\text{ mA}, I_B = 0$	-60 -80			V
Collector-emitter cutoff current (E-B short)	2SB0930 2SB0930A	I_{CES} $V_{CE} = -60\text{ V}, V_{BE} = 0$ $V_{CE} = -80\text{ V}, V_{BE} = 0$			-400 -400	μA
Collector-emitter cutoff current (Base open)	2SB0930 2SB0930A	I_{CEO} $V_{CE} = -30\text{ V}, I_B = 0$ $V_{CE} = -60\text{ V}, I_B = 0$			-700 -700	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio	h_{FE1}^* h_{FE2}	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$ $V_{CE} = -4\text{ V}, I_C = -3\text{ A}$	70 15		250	—
Base-emitter voltage	V_{BE}	$V_{CE} = -4\text{ V}, I_C = -3\text{ A}$			-2.0	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4\text{ A}, I_B = -0.4\text{ A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 10\text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -4\text{ A}$		0.2		μs
Storage time	t_{stg}	$I_{B1} = -0.4\text{ A}, I_{B2} = 0.4\text{ A}$		0.5		μs
Fall time	t_f	$V_{CC} = -50\text{ V}$		0.2		μs

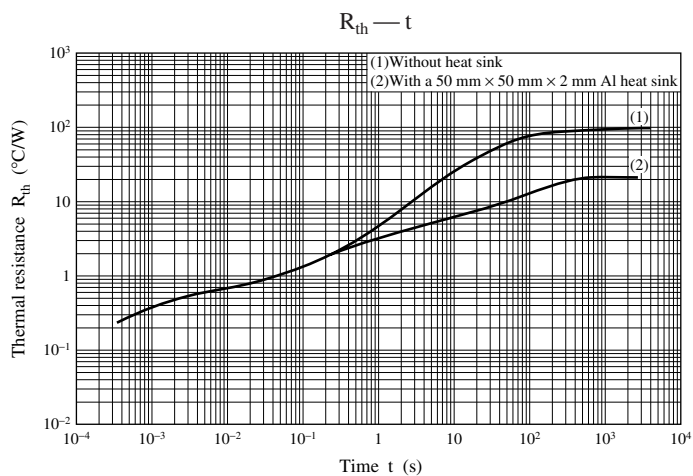
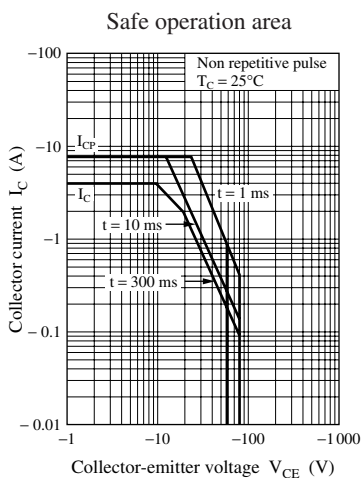
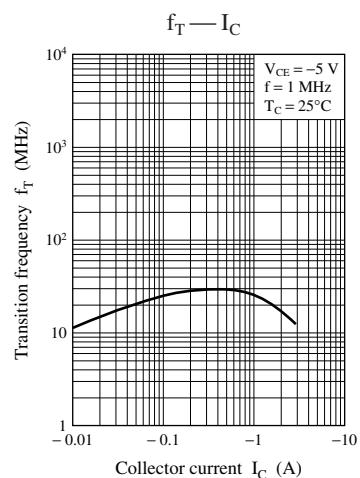
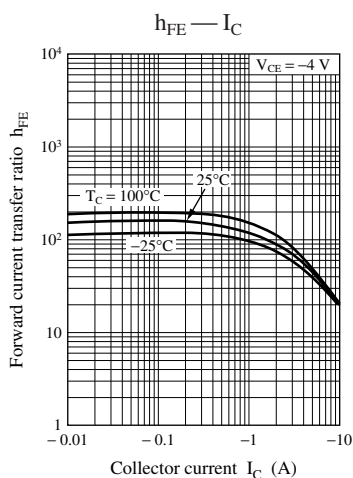
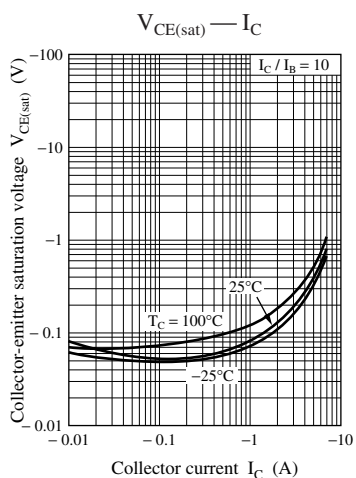
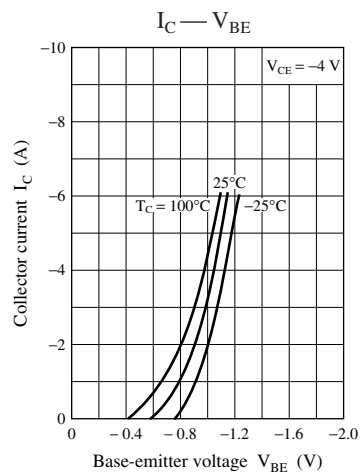
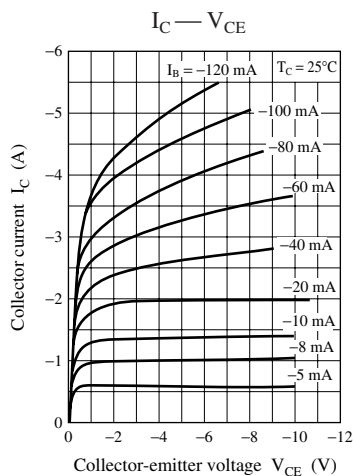
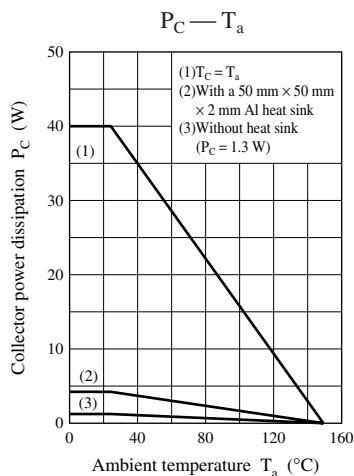
(Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *. Rank classification

Rank	Q	P
h_{FE1}	70 to 150	120 to 250

(Note) The part number in the parenthesis shows conventional part number.



(Note) Self-supported type package is also prepared.



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